Electronic Supplementary Information (ESI) for

Charge transfer doping with an organic layer to achieve a high-performance p-type WSe_2 transistor

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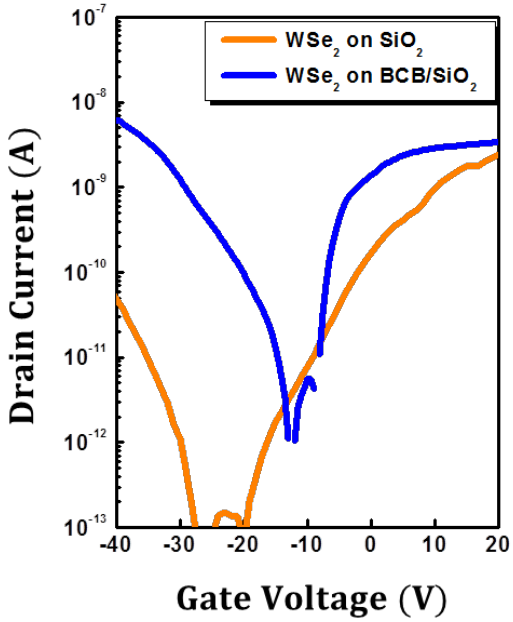

Fig. S1. Transfer characteristics of WSe_2 transistors with (blue) and without (orange) a BCB layer.

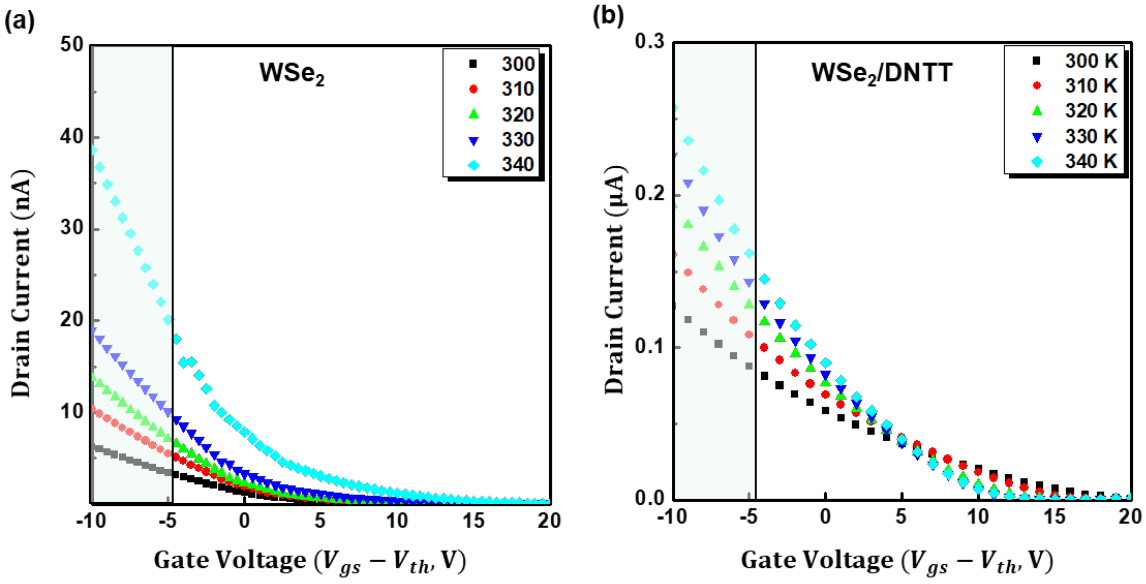

Fig. S2. Extraction of field-effect mobility of the (a) WSe_2 FET and (b) WSe_2/DNTT FET. After extracting the threshold voltages of the devices, the transfer characteristics of the devices are retraced as a function of the gate overdrive voltage ($V_{gs} - V_{th}$). The field-effect mobility is estimated from the slopes within the −5 to −10 V overdrive voltage range.